AiT Semiconductor Inc.

### DESCRIPTION

The AH8115 is an integrated hall-effect sensor designed specifically to meet the requirements of low-power devices. e.g. as an On/Off switch in cellular flip-phones, with battery operating voltages of 2.0V-5.5V.

Precise magnetic switching points and high temperature stability are achieved through the unique design of the internal circuit. An onboard clock scheme is used to reduce the average operating current of the IC. During the operate phase the IC compares the actual magnetic field detected with the internally compensated switching points. The output Voltage is switched at the end of each operating phase. During the Stand-by phase the output stage is latched and the current consumption of the device reduced to some  $\mu A$ .

The IC switching behavior is omnipolar, it can be switched on with either the north or south pole of a magnet.

AH8115 is higher sensitivity of magnetic induction than AH8113, it can be used in security systems, sensing magnet smaller occasions.

The AH8115 is available in TSOT-23 package.

#### **ORDERING INFORMATION**

Package Type	Part Number			
TSOT-23	TEO	AH8115TE3R		
SPQ: 4,000pcs/Reel	TE3	AH8115TE3VR		
Nata	V: Halogen free Package			
Note	R: Tape & Reel			
AiT provides all RoHS products				

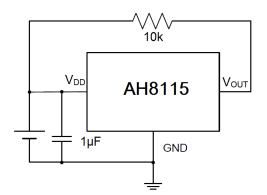
### FEATURES

- Micro power design
- 2.0V to 5.5V battery operation
- High sensitivity and high stability of the magnetic switching points
- High resistance to mechanical stress
- Digital output signal
- Switching for both poles of a magnet (omnipolar)
- Not suitable for automotive application
- Operating temperature range
- $T_{\text{MIN}} \le T_{\text{A}} \le T_{\text{MAX}} \qquad -40^{\circ}\text{C} \le T_{\text{A}} \le 85^{\circ}\text{C}$
- Operating voltage range  $2.0V \le V_{DD} \le 6.0V$
- Available in TSOT-23 package

#### APPLICATION

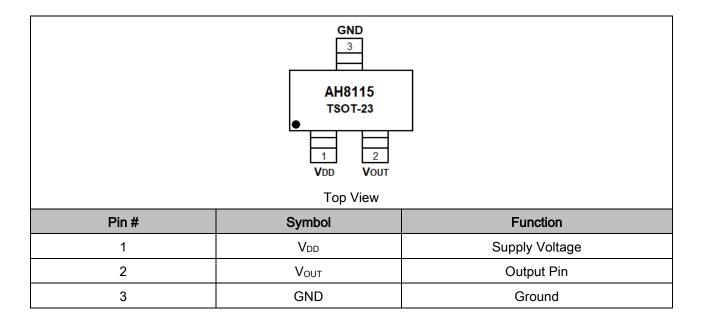
- Mobile phones
- Notebook
- Portable electronic devices

### TYPICAL APPLICATION





# PIN DESCRIPTION





## ABSOLUTE MAXIMUM RATINGS

V <sub>DD</sub> , Supply Voltage	2.0V~6.0V
IDD, Operating Current	-1mA~4.5mA
Vour, Output Voltage	-0.3V~6.0V
Iout, Output Current	-1mA~2.0mA
Ts, Storage Temperature Range	-40°C ~ +150°C
T <sub>J</sub> , Maximum Junction Temperature	150°C
ESD Protection	4kV

Stress beyond above listed "Absolute Maximum Ratings" may lead permanent damage to the device. These are stress ratings only and operations of the device at these or any other conditions beyond those indicated in the operational sections of the specifications are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

### ELECTRICAL CHARACTERISTICS

T<sub>A</sub>=+25°C,V<sub>DD</sub>=3.0V, unless otherwise specified

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Supply Voltage	V <sub>DD</sub>		2.0	-	5.5	V
Averaged Supply Current	Isavg		1	3	10	μA
Averaged Current During Operating Time	ISOPAVG		0.5	2.0	3.5	mA
Peak Current During Operating Time	I <sub>SOPT</sub>		-	-	4.5	mA
Supply Current During Standby Time	ISSTB		1	1.9	8	μA
Output Saturation Voltage	V <sub>QSAT</sub>	I <sub>OUT</sub> =1mA	-	0.13	0.4	V
Output on Leakage Current	Iqleak		-	0.01	1	μA
Output Rise Time	tr	R∟=2.7kΩ, C∟=10pF	-	0.5	1	μs
Output Fall Time	r <sub>f</sub>	$R_L=2.7k\Omega$ , $C_L=10pF$	-	0.1	1	μs
Operating Time	t <sub>op</sub>		25	100	160	μs
Standby Time	t <sub>stb</sub>		60	140	240	ms
Duty Cycle	t <sub>op</sub> /t <sub>stb</sub>		-	0.071	-	%
Start-up Time of IC	<b>t</b> stu		-	12	20	μs

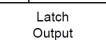


### MANGENTIC CHARACTERISTICS

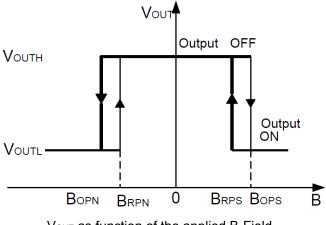
T <sub>A</sub> =+25°C,V <sub>DD</sub> =2.7V, Unless otherwise specified					
Symbol	Min.	Тур. Мах.		Unit	
B <sub>OPS</sub>	1	1.5	2	mT	
Bopn	-2	-1.5	-1	mT	
B <sub>RPS</sub>	0.8	1.1	1.5	mT	
Brpn	-1.8	-1.1	-0.8	mT	
Внуз	0.1	0.4	0.7	mT	

BHYS 0.1 0.4 0.7

100µs



t

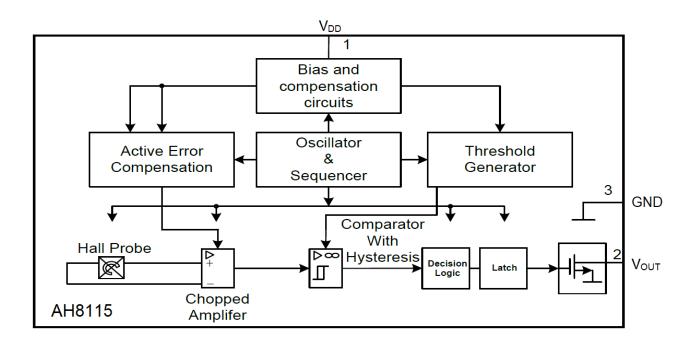


130ms

Vout as function of the applied B-Field



## **BLOCK DIAGRAM**

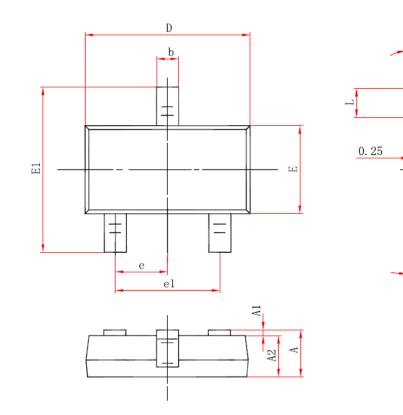




θ

# PACKAGE INFORMATION

Dimension in TSOT-23 (Unit: mm)



Symbol	Millimeters		Inches		
	Min	Max	Min	Max	
А	0.700	0.900	0.028	0.035	
A1	0.000	0.100	0.000	0.004	
A2	0.700	0.800	0.028	0.031	
b	0.350	0.500	0.014	0.020	
с	0.080	0.200	0.003	0.008	
D	2.820	3.020	0.111	0.119	
E	1.600	1.700	0.063	0.067	
E1	2.650	2.950	0.104	0.116	
е	0.95 BSC		0.037 BSC		
e1	1.90 BSC		0.075 BSC		
L	0.300	0.600	0.012	0.024	
θ	0°	8°	0°	8°	



### IMPORTANT NOTICE

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